

# Vasilev Aa

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

16  
papers

163  
citations

8  
h-index

12  
g-index

17  
ext. papers

233  
ext. citations

3.3  
avg, IF

2.7  
L-index

#	Paper	IF	Citations
16	Electrical properties of $\text{Ga}_2\text{O}_3$ films grown by halide vapor phase epitaxy on sapphire with $\text{Cr}_2\text{O}_3$ buffers. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 215701	2.5	1
15	Structural and electrical properties of thick $\text{Ga}_2\text{O}_3$ grown on GaN/sapphire templates. <i>APL Materials</i> , <b>2022</b> , 10, 061102	5.7	1
14	1 GeV proton damage in $\text{Ga}_2\text{O}_3$ . <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 185701	2.5	1
13	Parasitic p-n junctions formed at V-pit defects in p-GaN. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 155702	2.5	1
12	Experimental estimation of electron-hole pair creation energy in $\text{Ga}_2\text{O}_3$ . <i>Applied Physics Letters</i> , <b>2021</b> , 118, 202106	3.4	8
11	Electrical properties and deep trap spectra in $\text{Ga}_2\text{O}_3$ films grown by halide vapor phase epitaxy on p-type diamond substrates. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 185701	2.5	6
10	Crystal orientation dependence of deep level spectra in proton irradiated bulk $\text{Ga}_2\text{O}_3$ . <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 035701	2.5	4
9	Photosensitivity of $\text{Ga}_2\text{O}_3$ Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , <b>2020</b> , 8, 111105	5.7	13
8	Anisotropy of hydrogen plasma effects in bulk n-type $\text{Ga}_2\text{O}_3$ . <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 175702	2.5	14
7	Pulsed fast reactor neutron irradiation effects in Si doped n-type $\text{Ga}_2\text{O}_3$ . <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 274001	3	13
6	Electric field dependence of major electron trap emission in bulk $\text{Ga}_2\text{O}_3$ : Poole-Frenkel effect versus phonon-assisted tunneling. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 304001	3	9
5	Editors' Choice Electrical Properties and Deep Traps in $\text{Ga}_2\text{O}_3$ :Sn Films Grown on Sapphire by Halide Vapor Phase Epitaxy. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 045003	2	10
4	Defects at the surface of $\text{Ga}_2\text{O}_3$ produced by Ar plasma exposure. <i>APL Materials</i> , <b>2019</b> , 7, 061102	5.7	25
3	Deep trap spectra of Sn-doped $\text{Ga}_2\text{O}_3$ grown by halide vapor phase epitaxy on sapphire. <i>APL Materials</i> , <b>2019</b> , 7, 051103	5.7	22
2	Hydrogen plasma treatment of $\text{Ga}_2\text{O}_3$ : Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 032101	3.4	29
1	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of $\text{Ga}_2\text{O}_3$ . <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, P661-P666	2	4